ΡΛΝ	JIT
	SEMI
	CONDUCTOR

## 40V N-Channel Enhancement Mode MOSFET

Current

61 A

Voltage

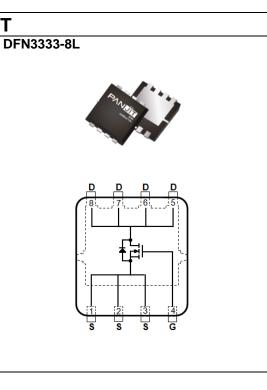
40 V

#### Features

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@15A<6.3m\Omega$
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@7V, I<sub>D</sub>@10A<7.7mΩ
- Excellent FOM
- Standard Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.03 grams



#### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	40	
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Continuous Drain Current <sup>(Note 3)</sup>	Tc=25°C		61	
	Tc=100°C	I <sub>D</sub>	43	А
Pulsed Drain Current <sup>(Note 1)</sup>	T <sub>C</sub> =25°C	I <sub>DM</sub>	244	
Power Dissipation	T <sub>C</sub> =25°C	5	42	
	Tc=100°C	PD	21	W
Continuous Droin Curront(Note 4)	T <sub>A</sub> =25 <sup>o</sup> C	15	٨	
Continuous Drain Current <sup>(Note 4)</sup>	T <sub>A</sub> =70°C	I <sub>D</sub>	12.4	A
Devue Dissis ation	T <sub>A</sub> =25°C		2.5	14/
Power Dissipation	T <sub>A</sub> =70 <sup>°</sup> C	PD	1.8	W
Single Pulse Avalanche Energy <sup>(Note</sup>	9 5)	Eas	85	mJ
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~175	°C
Thermal Resistance <sup>(Note 4)</sup>	Junction to Case	R <sub>θJC</sub>	3.6	°C/W
	Junction to Ambient	R <sub>θJA</sub>	60	C/VV



#### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static	•		·				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	Vgs=0V, Id=250uA	40	-	-	V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =50uA	2	2.8	3.5	V	
Drain-Source On-State Resistance		Vgs=10V, Id=15A	-	5	6.3		
	R <sub>DS(on)</sub>	V <sub>GS</sub> =7V, I <sub>D</sub> =10A	-	- 5.9 7.7		mΩ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA	
Dynamic <sup>(Note 6)</sup>	-	-	-	•	•		
Total Gate Charge	Qg	$V_{DS}=32V, I_{D}=15A,$	-	23	-		
Gate-Source Charge	Qgs		-	5	-	nC	
Gate-Drain Charge	$Q_gd$	V <sub>GS</sub> =10V <sup>(Note 2,3)</sup>	-	6	-		
Input Capacitance	Ciss		-	1283	-		
Output Capacitance	Coss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,	-	252	-	pF	
Reverse Transfer Capacitance	Crss	f=1MHZ	-	45	-		
Gate resistance	Rg	f=1MHZ	-	0.8	-	Ω	
Turn-On Delay Time	td <sub>(on)</sub>		-	14	-		
Turn-On Rise Time	tr	V <sub>DS</sub> =32V, I <sub>D</sub> =15A,	-	3	-		
Turn-Off Delay Time	td <sub>(off)</sub>	V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω (Note 2,3)	-	24	-	ns	
Turn-Off Fall Time	tf	(Note 2,3)	-	5	-		
Drain-Source Diode		·					
Diode Forward Current	I <sub>S</sub>	T 05°0	-	-	61		
Pulsed Diode Forward Current	I <sub>SM</sub>	Tc=25°C	-	-	244	A	
Diode Forward Voltage	V <sub>SD</sub>	Is=20A, V <sub>GS</sub> =0V	-	0.85	1.3	V	
Reverse Recovery Time	Trr	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	24	-	ns	
Reverse Recovery Charge	Qrr	dl <sub>s</sub> /dt=100A/us	-	11	-	nC	

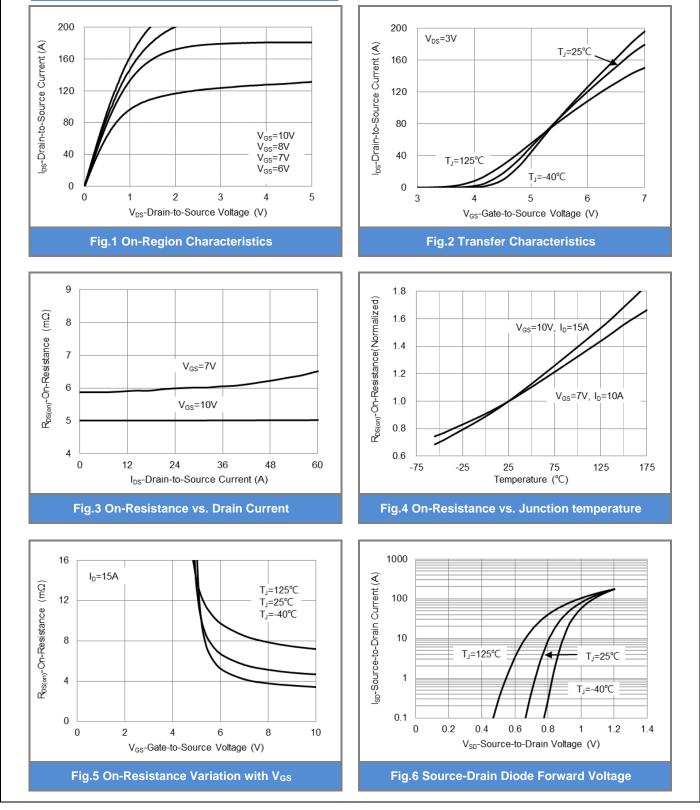
NOTES :

- 1. Pulse width100us, Duty cycle<2%.</td>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an R\_{\rm BJC}=3.6^{\circ}C/W.
- 4.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH,  $I_{AS}$ =18A,  $V_{DD}$ =30V,  $V_{GS}$ =10V, Starting T\_J=25°C.
- 6. Guaranteed by design, not subject to production testing.

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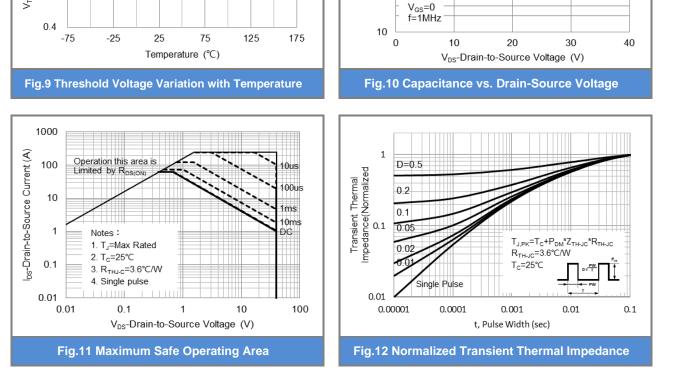
PJQ4546VP-AU

**TYPICAL CHARACTERISTIC CURVES** 



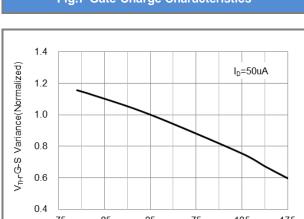
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#### **TYPICAL CHARACTERISTIC CURVES** 10 V<sub>DS</sub>=32V V<sub>GS</sub>-Gate-to-Source Voltage (V) I<sub>D</sub>=15A 8 6 4 2 0 5 0 10 15 20 25 Qg (nC)

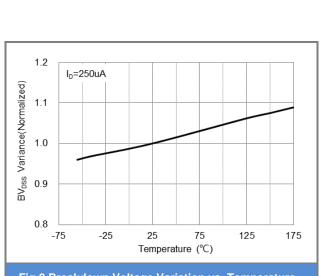




10000 Ciss Capacitance (pF) 001  $C_{oss}$ 

Crss





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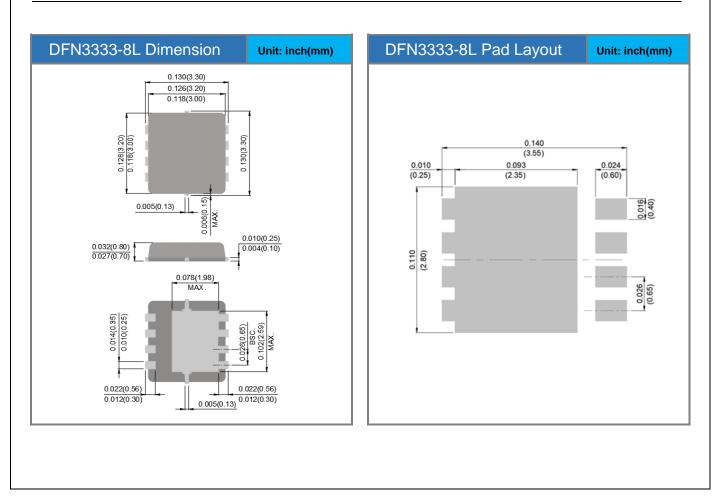




#### **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking	
PJQ4546VP-AU	DFN3333-8L	5K pcs / 13" reel	546V	

#### Packaging Information & Mounting Pad Layout





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